



## STPS10150CT/CG

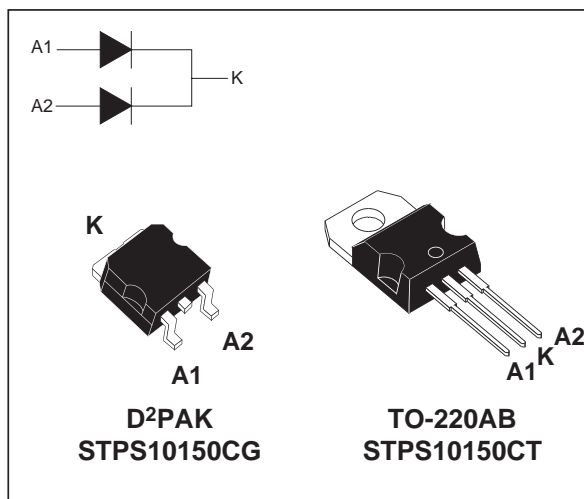
### HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

#### MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 5 A
$V_{RRM}$	150 V
$T_j$	175°C
$V_F(max)$	0.75 V

#### FEATURES AND BENEFITS

- HIGH JUNCTION TEMPERATURE CAPABILITY
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- LOW LEAKAGE CURRENT
- AVALANCHE CAPABILITY SPECIFIED



#### DESCRIPTION

Dual center tap schottky rectifier designed for high frequency Switched Mode Power Supplies.

#### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter				Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage				150	V
I <sub>F(RMS)</sub>	RMS forward current				10	A
I <sub>F(AV)</sub>	Average forward current δ = 0.5	TO-220AB D <sup>2</sup> PAK	Tc = 155°C	per diode per device	5 10	A
I <sub>FSM</sub>	Surge non repetitive forward current		tp = 10 ms   sinusoidal		120	A
P <sub>ARM</sub>	Repetitive peak avalanche power		tp = 1μs   Tj = 25°C		3100	W
T <sub>stg</sub>	Storage temperature range				- 65 to + 175	°C
Tj	Maximum operating junction temperature				175	°C
dV/dt	Critical rate of rise of reverse voltage				10000	V/μs

## THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AB / D <sup>2</sup> PAK	Per diode	4	°C/W
		TO-220AB / D <sup>2</sup> PAK	Total	2.4	
$R_{th(c)}$		TO-220AB / D <sup>2</sup> PAK	Coupling	0.7	

When the diodes 1 and 2 are used simultaneously :  
 $\Delta T_{j(\text{diode } 1)} = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

## STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			2.0	$\mu\text{A}$
		$T_j = 125^\circ\text{C}$			0.40	2.0	mA
$V_F^{**}$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 5\text{ A}$			0.92	V
		$T_j = 125^\circ\text{C}$	$I_F = 5\text{ A}$		0.69	0.75	
		$T_j = 25^\circ\text{C}$	$I_F = 10\text{ A}$			1	
		$T_j = 125^\circ\text{C}$	$I_F = 10\text{ A}$		0.79	0.85	

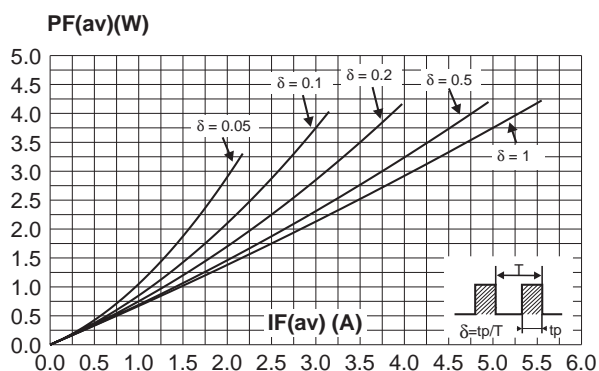
Pulse test : \*  $t_p = 5\text{ ms}$ ,  $\delta < 2\%$

\*\*  $t_p = 380\text{ }\mu\text{s}$ ,  $\delta < 2\%$

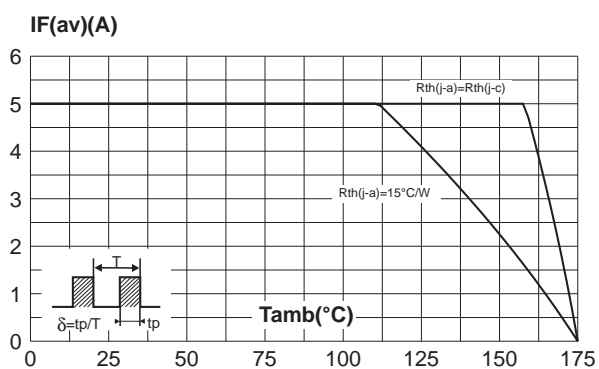
To evaluate the conduction losses use the following equation:

$$P = 0.65 I_{F(AV)} + 0.02 I_F^2(RMS)$$

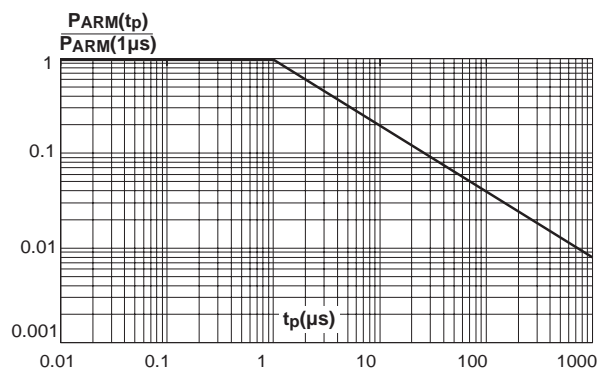
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



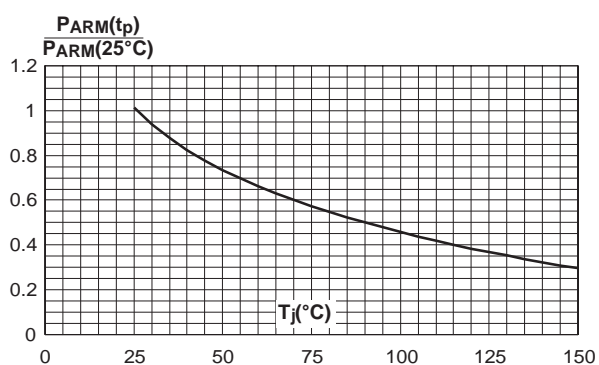
**Fig. 2:** Average forward current versus ambient temperature ( $\delta = 0.5$ , per diode).



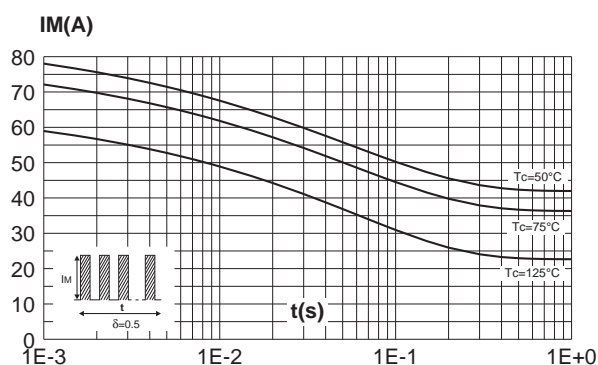
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



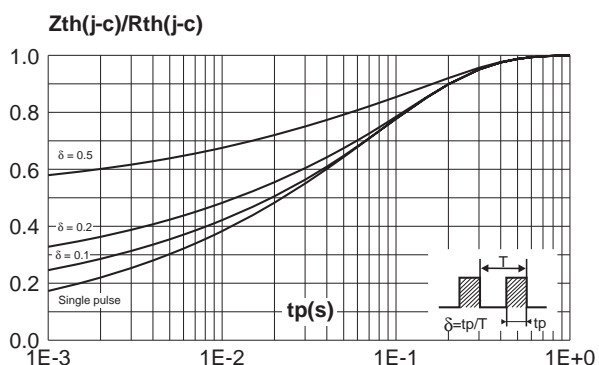
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



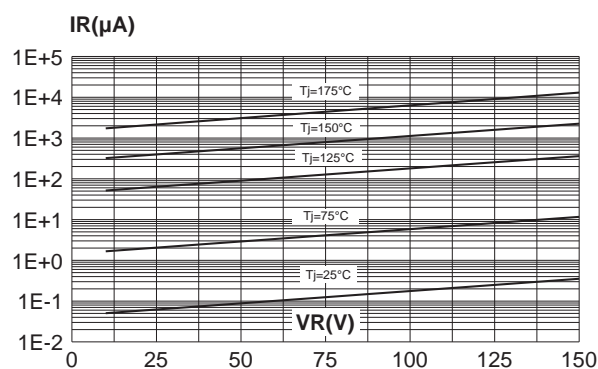
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values, per diode).



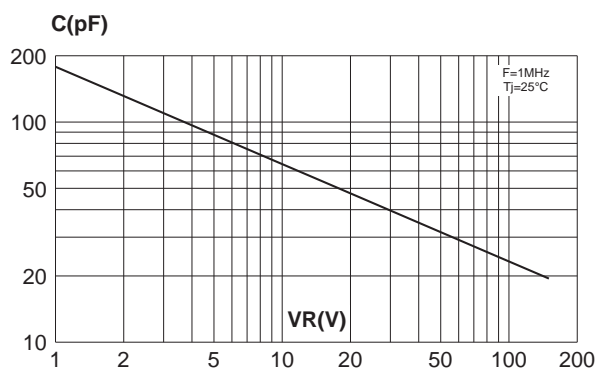
**Fig. 6:** Relative variation of thermal impedance junction to case versus pulse duration (per diode).



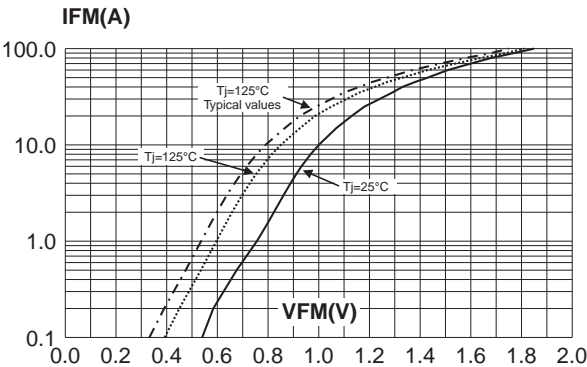
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values, per diode)



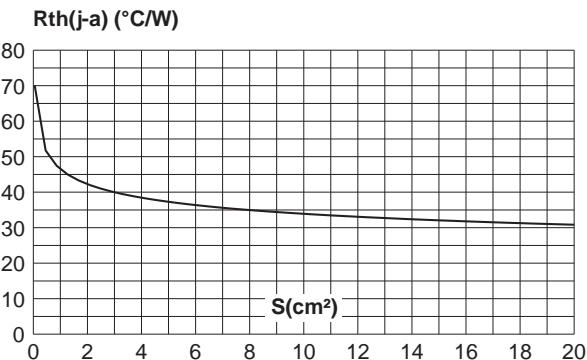
**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values, per diode).



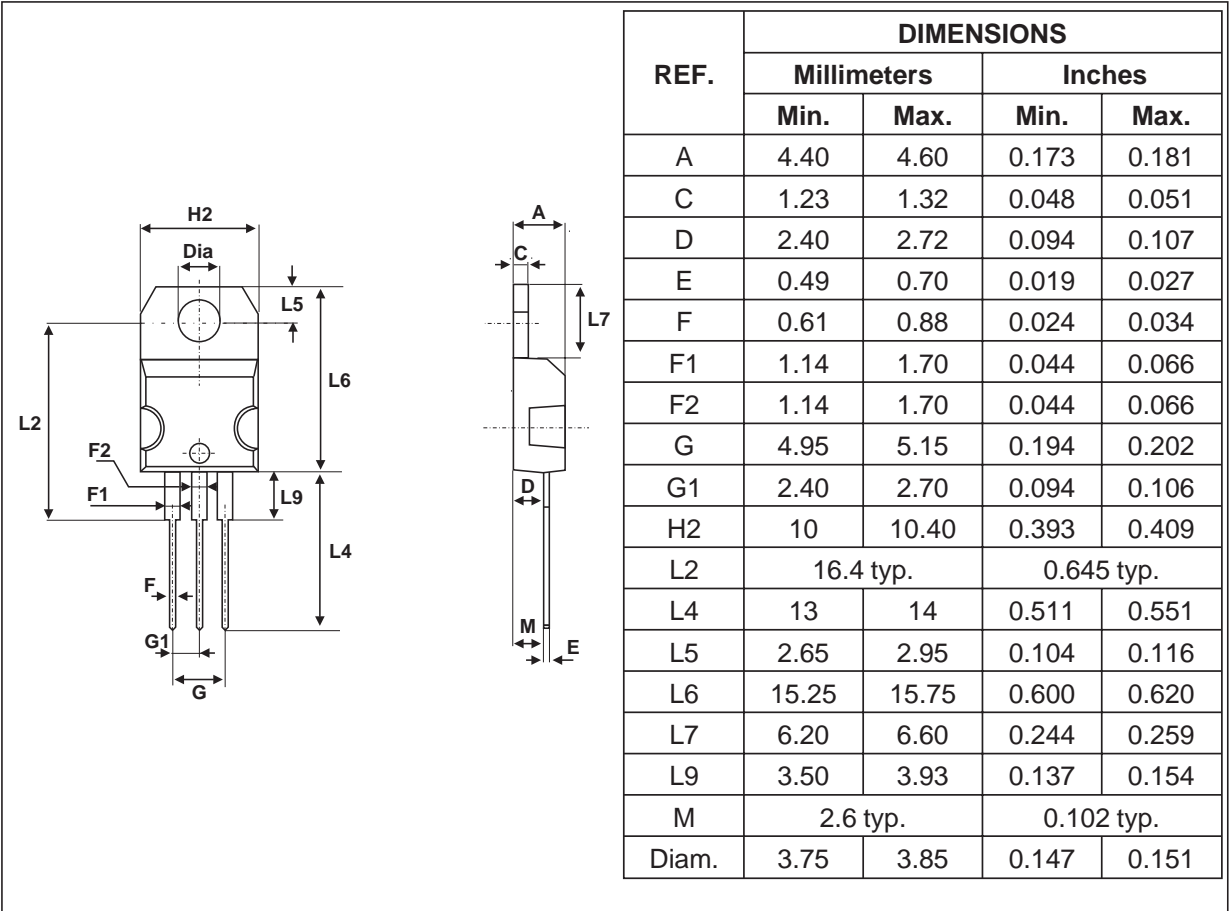
**Fig. 9:** Forward voltage drop versus forward current (maximum values, per diode).

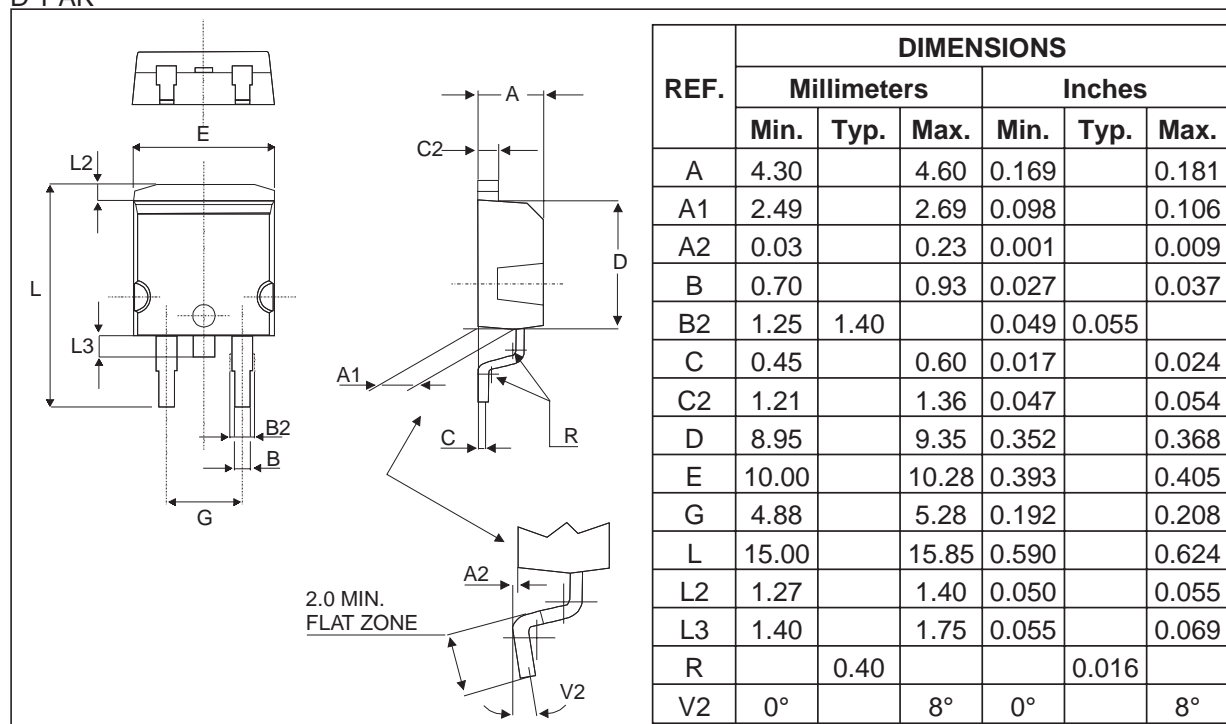
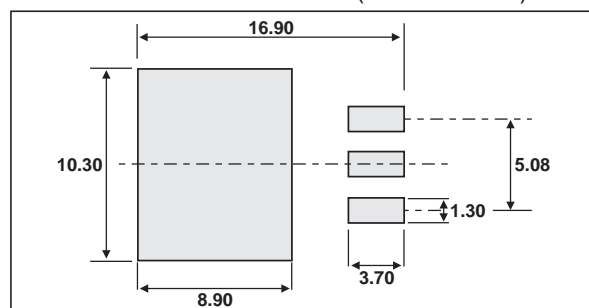


**Fig. 10:** Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board, copper thickness: 35µm) (STPS10150CG only).



**PACKAGE MECHANICAL DATA**  
TO-220AB



**PACKAGE MECHANICAL DATA**  
**D<sup>2</sup>PAK**

**FOOT PRINT DIMENSIONS (in millimeters)**


Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS10150CT	STPS10150CT	TO-220AB	2.2 g	50	Tube
STPS10150CG	STPS10150CG	D <sup>2</sup> PAK	1.48 g	50	Tube
STPS10150CG-TR	STPS10150CG	D <sup>2</sup> PAK	1.48 g	1000	Tape & reel

**■ EPOXY MEETS UL94, V0**

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